



LAPD-1-06-17-CHIP



TECHNICAL DATA

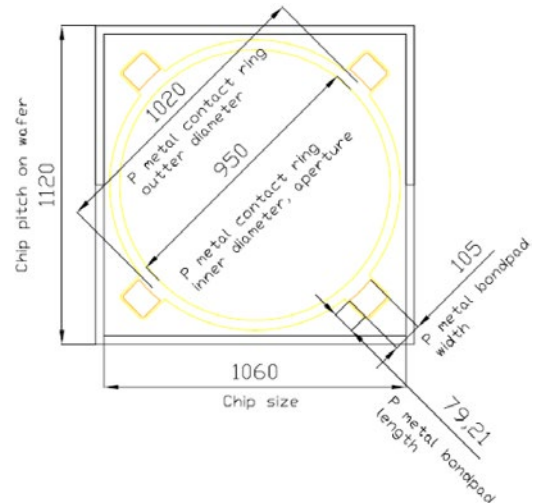
Photodiode Chip die	InGaAs
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LAPD-1-06-17-CHIP adopt InGaAs pin structure based on InP by MOCVD method and planar diffusing technology. The active area is Ø 1 mm respectively.



Absolute Maximum Ratings

Item	Symbol	Value	Unit
Reverse Voltage	U_R	20	V
Reverse Current	I_R	20	mA
Forward current	I_F	10	mA
Operating Temperature	T_{opr}	-20 ... +85	°C
Storage Temperature	T_{std}	-40 ... +85	°C



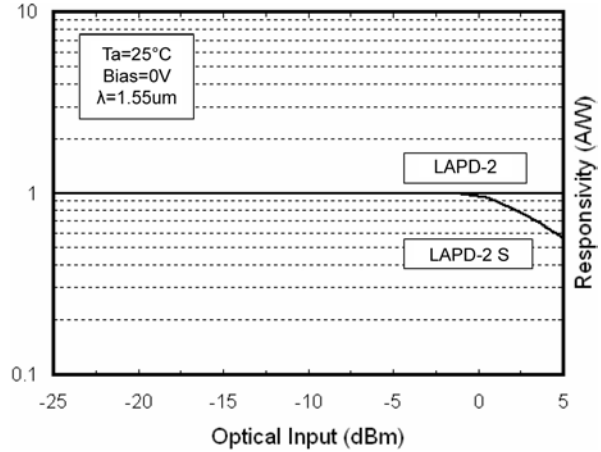
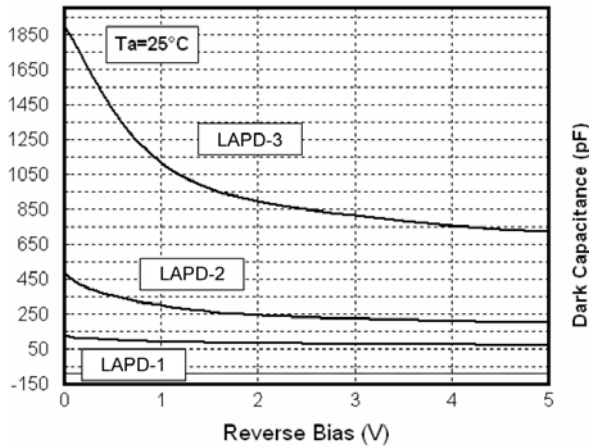
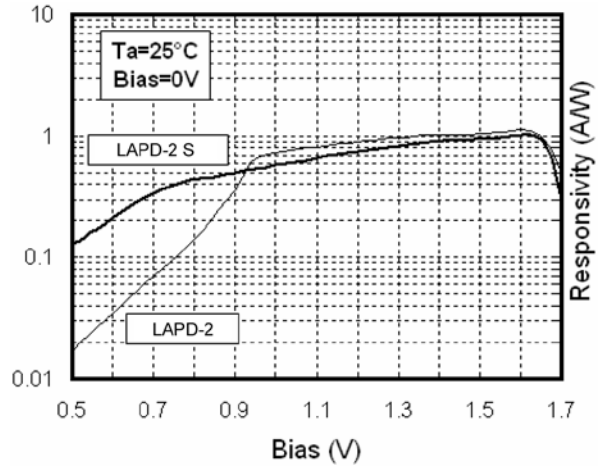
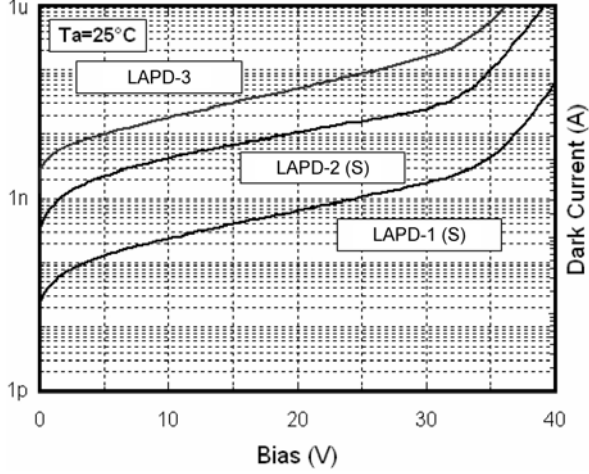
Specifications

Item	Min.	Typ.	Max.	Unit	
Wavelength Range	0.6 .. 1.7			µm	
Active Area	Ø 1			mm	
Saturation Power	1550 nm	-	-8	-	dBm
Specific Detectivity (D*)	1550 nm	2.5	5	-	10 ¹² Jones
Responsibility (0 V)	650 nm	0.20	0.30	-	A/W
	850 nm	0.40	0.50	-	
	1310 nm	0.80	0.90	-	
	1550 nm	0.85	0.95	-	
Capacitance	0 V	-	140	200	pF
	-5 V	-	70	100	
Dark Current	-5 V	-	2	10	nA
Shunt Resistance		25	80	-	MΩ
Chip Size	1060 x 1060			µm	
Chip Thickness	300			µm	

Packing: Chips on adhesive film



Typical Performance Curves



LAPD-2 Spatial Response
 Ta=25°C, Bias=0V, λ=1550nm

